



SANYO Semiconductors

DATA SHEET

2SK2632LS

N-Channel Silicon MOSFET

General-Purpose Switching Device Applications

Features

- Low ON-resistance.
- Low Qg.
- Ultrahigh-speed switching.

Specifications

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	V _{DSS}		800	V
Gate-to-Source Voltage	V _{GSS}		±30	V
Drain Current (DC)	I _D		2.5	A
Drain Current (Pulse)	I _{DP}	PW≤10μs, duty cycle≤1%	7.5	A
Allowable Power Dissipation	P _D		2.0	W
		T _c =25°C	25	W
Channel Temperature	T _{ch}		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C

Electrical Characteristics at Ta=25°C

Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	I _D =1mA, V _{GS} =0V	800			V
Zero-Gate Voltage Drain Current	I _{DSS}	V _{DS} =800V, V _{GS} =0V			1.0	mA
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
Cutoff Voltage	V _{GS(off)}	V _{DS} =10V, I _D =1mA	3.5		5.5	V
Forward Transfer Admittance	y _{fs}	V _{DS} =10V, I _D =1.3A	0.7	1.4		S
Static Drain-to-Source On-State Resistance	R _{DS(on)}	I _D =1.3A, V _{GS} =15V		3.6	4.8	Ω

Marking : K2632

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SANYO Semiconductor Co., Ltd.

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2SK2632LS

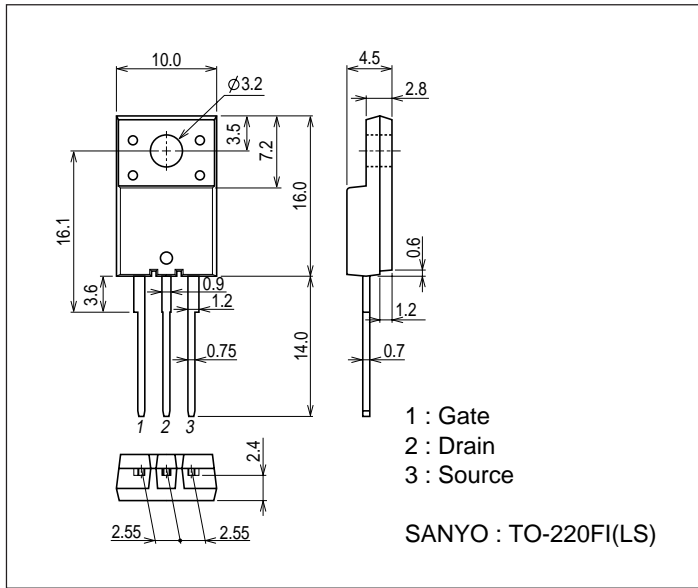
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Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Input Capacitance	Ciss	V _{DS} =20V, f=1MHz		550		pF
Output Capacitance	Coss	V _{DS} =20V, f=1MHz		150		pF
Reverse Transfer Capacitance	Crss	V _{DS} =20V, f=1MHz		70		pF
Total Gate Charge	Qg	V _{DS} =200V, I _D =2.5A, V _{GS} =10V		15		nC
Turn-ON Delay Time	t _{d(on)}	See specified Test Circuit.		15		ns
Rise Time	t _r	See specified Test Circuit.		15		ns
Turn-OFF Delay Time	t _{d(off)}	See specified Test Circuit.		45		ns
Fall Time	t _f	See specified Test Circuit.		23		ns
Diode Forward Voltage	V _{SD}	I _S =2.5A, V _{GS} =0V		0.84	1.2	V

Package Dimensions

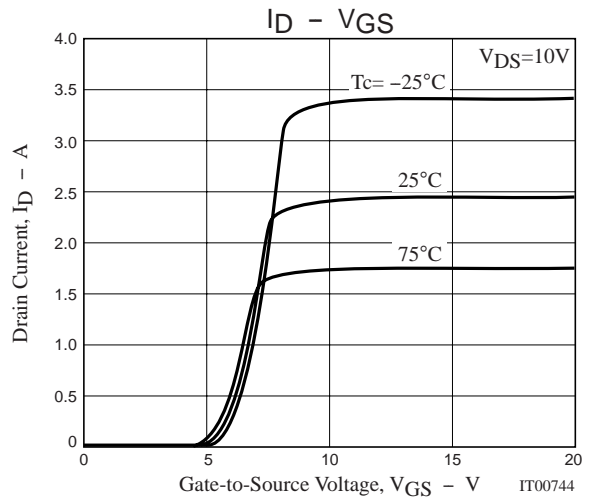
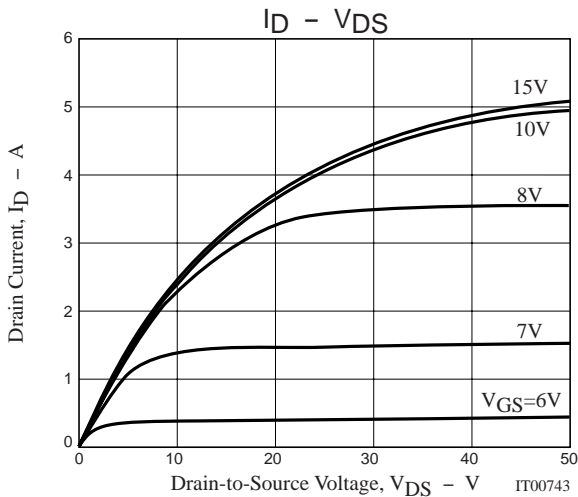
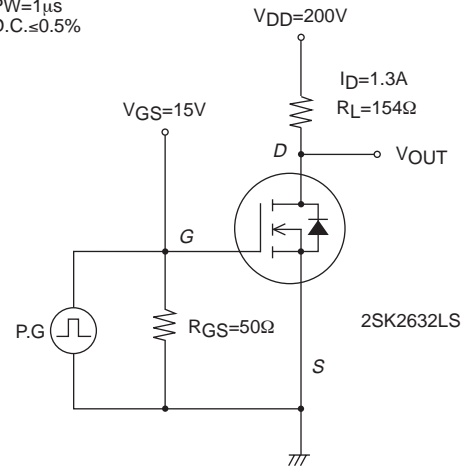
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7509-002

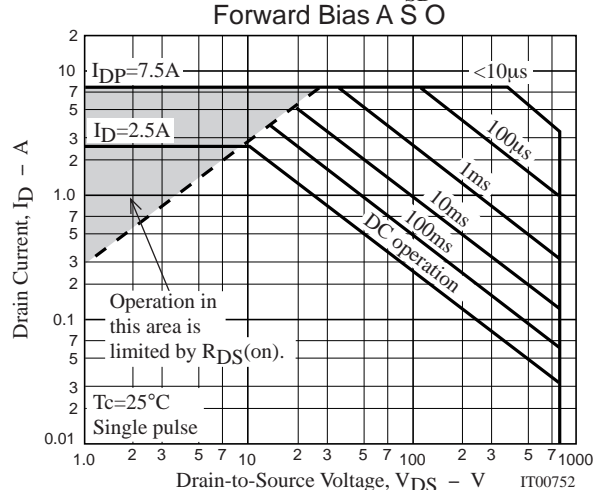
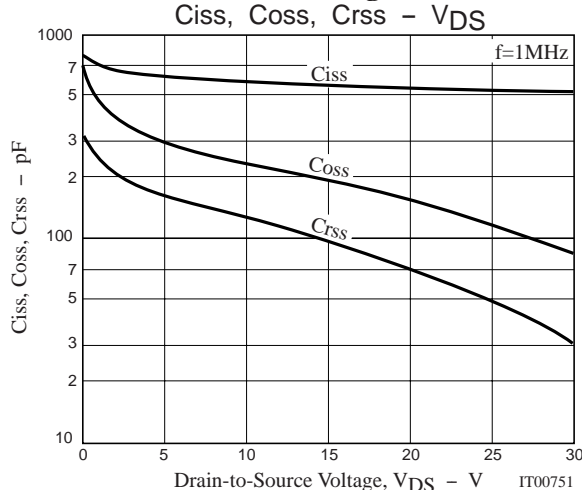
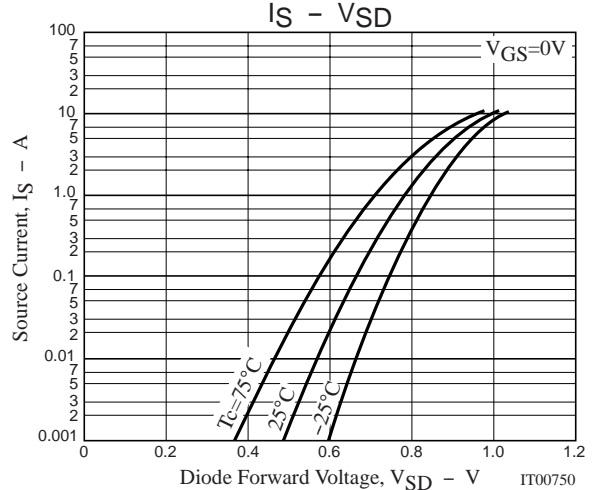
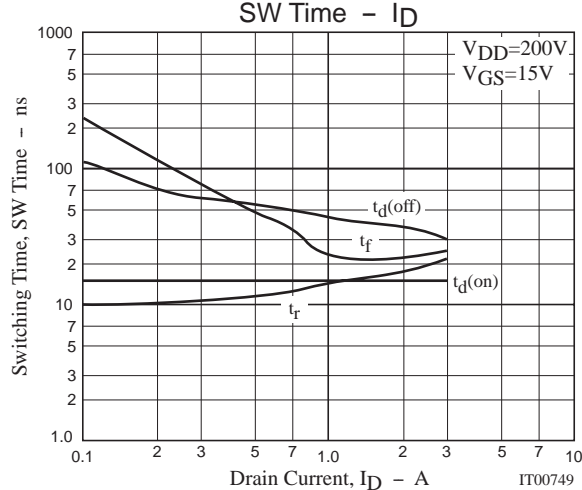
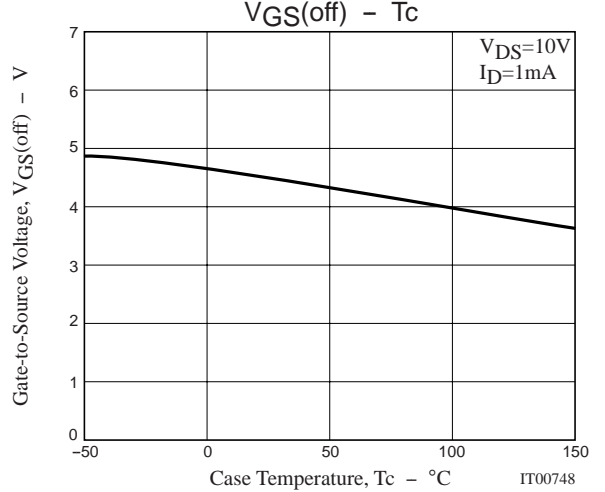
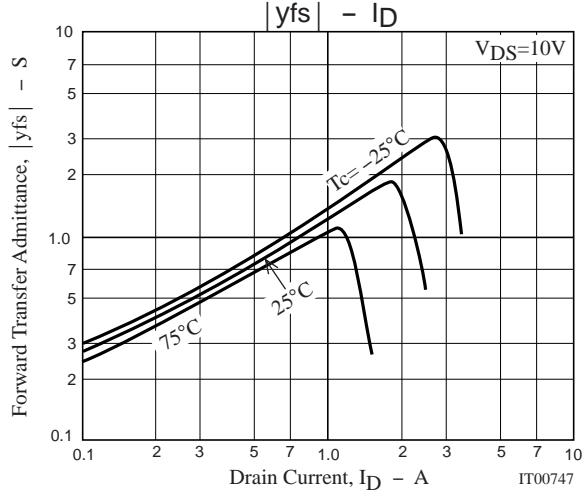
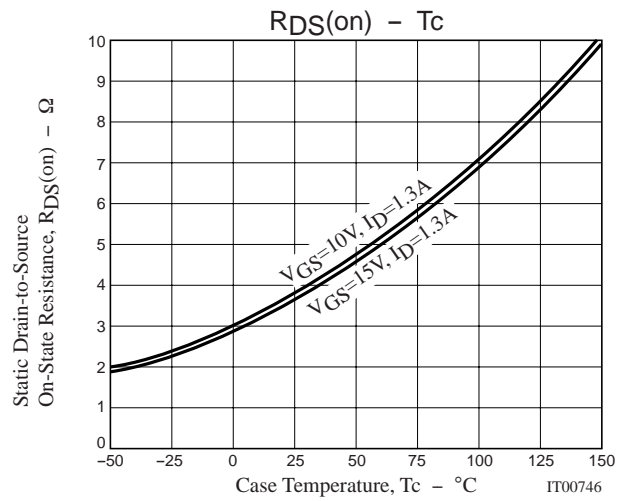
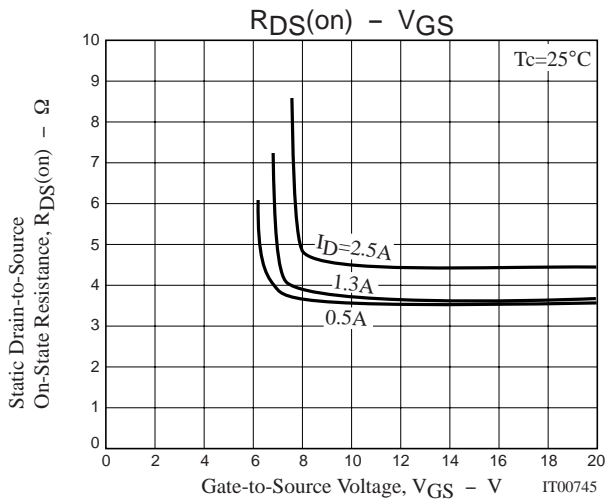


Switching Time Test Circuit

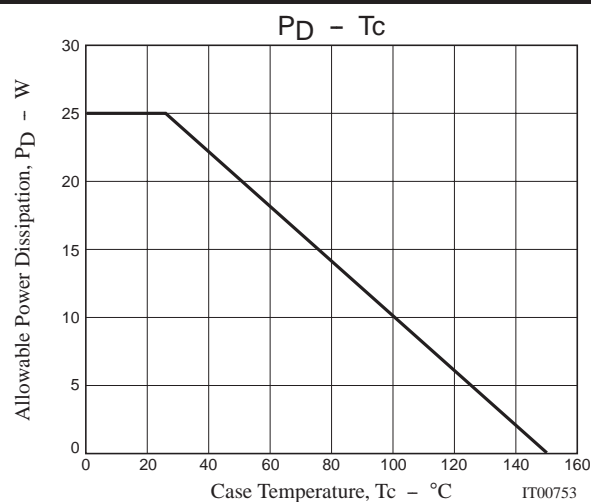
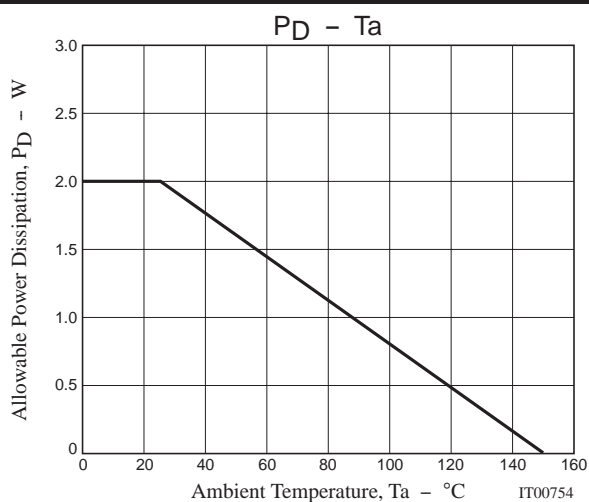
PW=1μs
D.C.≤0.5%



2SK2632LS



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Note on usage : Since the 2SK2632LS is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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